



KAMAKURA, JAPAN

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## Second Call for Papers

2017 International Conference on Simulation of  
Semiconductor Processes and Devices

# SISPAD2017

September 7 – 9, 2017

Workshop, September 6

Kamakura Prince Hotel, Kamakura, JAPAN



Sponsored by Japan Society of Applied Physics

Technical Co-sponsored by The IEEE Electron Device Society



**Scope:**

This conference provides an opportunity for the presentation and discussion of the latest advances in modeling and simulation of semiconductor devices, processes, and equipment for integrated circuits.

**Topics:**

- Modeling and simulation of all sorts of semiconductor devices, including FinFETs, GAA FETs, ultra-thin SOI devices, emerging memory devices, new-material-based nanodevices, optoelectronic devices, TFTs, sensors, power electronic devices, spintronic devices, tunnel FETs, SETs, organic electronic devices, and bioelectronic devices
- Modeling and simulation of all sorts of semiconductor processes, including first-principles material design and growth simulation of nano-scale fabrication
- Fundamental aspects of device modeling and simulation, including quantum transport, thermal transport, fluctuation, noise, and reliability
- Compact modeling for circuit simulation, including low-power, high frequency, and power electronics applications
- Process/device/circuit co-simulation in context with system design and verification
- Equipment, topography, lithography modeling
- Interconnect modeling, including noise and parasitic effects
- Numerical methods and algorithms, including grid generation, user-interface, and visualization
- Metrology for the modeling of semiconductor devices and processes

**Plenary Speakers:**

- Jean-Charles Barbe (Cea Leti) : Stacked Nanowires/Nanosheets GAA MOSFET from Technology to Design Enablement
- Sayeef Salahuddin (Univ California Berkeley) : Energy Efficient Computing with Hyperdimensional Vector Space Models
- Nobuyuki Sano (Tsukuba Univ) : Physical Issues in Device Modeling: Length Scale, Disorder, and Phase Interference

**Abstract Submission:**

Authors are invited to submit a two-page abstract (A4 size or 297×210 mm) including figures. Full submission information will be updated in the Second Call for Papers and the following web site.

<https://sites.google.com/site/sispad2017/>

Authors of accepted papers will be notified by May 31, 2017. Camera-ready copy of a four-page manuscript will be required from the authors for inclusion in the Conference Proceedings by June 30, 2017.

**Deadline for submission of abstract: April 10, 2017 (Extended)**

**Any inquiries on submission should be sent to:**

Akira Hiroki

Program Chair

hiroki@kit.ac.jp

Takashi Kurusu

Program Vice-Chair

takashi.kurusu@toshiba.co.jp

